

Product Features

- 2400 ~ 2500MHz (ISM band)
- 230W CW Psat @ 50V
- 74% Drain Efficiency @ 50V
- Excellent Ruggedness
- Excellent Thermal Stability
- Internally Matched

Applications

- · Industrial Heating and Drying
- Scientific
- Medical : Skin Treatment, Blood Therapy
- · Plasma Lighting



Package Type : NS-AS01

Description

The 200W CW RF Power Transistor is designed for Industrial, Scientific, Medical (ISM) and Plasma Lighting applications at 2450MHz. This device is suitable for use in CW, pulse and linear applications. This high efficiency rugged device is targeted to replace Industrial magnetrons and other vacuum tubes currently powering industrial heating, drying, plasma lighting and medical systems.

Typical CW Peak Power Performance $(V_{DS}=+50V, Tc=25^{\circ}C, 50\Omega)$

Frequency [MHz]	Signal Type	Pin [W]	Pin [W] Power Gain [dB]		Pout [W]
2400.0		12.5	13.1	76.6	254.1
2450.0	CW	10.4	13.8	74.9	251.4
2500.0		11.5	13.2	75.3	238.4

Absolute Maximum Ratings

Rating	Symbol	Value	Unit	Condition
Drain to Source Voltage	V _{DSS}	150	V	Tc=25°C
Gate to Source Voltage	V _{GS}	-10, +2	v	Tc=25°C
Operating Voltage	V_{DD}	52	V _{DC}	-
Maximum Forward Gate Current	Igmax	32	mA	Tc=25°C
Maximum Drain Current ^{*1}	I _{DMAX}	12	А	Tc=25°C
Power Dissipation	P _{DISS}	120	W	Tc=85°C
Storage Temperature	T _{STG}	-65, +150	°C	-
Case Operating Temperature	T _C	-40, +150	°C	-
Operating Junction Temperature ^{*2}	τ _J	225	°C	-
Soldering Temperature ^{*3}	Ts	245	°C	-

Note

*1 Current Limit for long term, reliable operation.

*2 Continuous use at maximum temperature will affect MTTF. *3 Refer to the Application Note(AN-002) on soldering - "Solder Condition for RFHIC's GaN Device"

Thermal Characteristics

Rating	Symbol	Value	Unit Cond	
Thermal Resistance, Junction to Case	R $_{ m BJC}$	1.17 *1	°C/W	Tc=85°C

Note

*1 Measured for the IE24200P at dissipation power is 120W



Characteristics	Conditions	Symbol	Min	Тур	Max	Unit		
DC Characteristics ^{*1}								
Gate Threshold Voltage	$V_{DS} = 10V$	V _{GS(TH)}	-3.8	-3.0	-2.3	V_{DC}		
Gate Threshold Voltage	I _D = 28.8mA	V GS(TH)						
Gate Quiescent Voltage	$V_{\rm DS} = 50V$	V _{GS(Q)}		2.2		V _{DC}		
Gate Quiescent voltage	$I_D = 50 mA$	V GS(Q)	-	-3.2	-	V DC		
Saturated Drain Current ^{*2}	$V_{DS} = 6V$	I _{DS}	24.0	28.8		А		
Saturateu Dram Current	$V_{GS} = 2V$	IDS	24.0			А		
Drain-Source Breakdown Voltage	$V_{GS} = -8V$	V _{BR}	150	-		V		
Dram-Source Breakuown voltage	$I_D = 41.8 mA$	v BK				•		
Gate Leakage Current	$V_{GS} = -8V$	I _{GLKG}	-6.3	-		mA		
Gate Leakage Current	$V_{DS} = 120V$	IGLKG						
Drain Leakage Current	$V_{GS} = -8V$	Idlkg	-	-	11.5	mA		
	$V_{\rm DS} = 120 V$	IDEKG			11.5	IIIA		
	RF Characteristic	s (Fc = 2450)MHz unless	otherwise note	d)			
Saturated Output Power ^{*3}	$V_{\rm DS} = 50V$	Psat	200	230	-	W		
Saturated Output Fower	$I_{DQ} = 50 mA$	I SAI	200			vv		
	$V_{DS} = 50V$							
CW Drain Efficiency*3	$I_{DQ} = 50 mA$	η	70	74	-	%		
W W	P _{OUT} = P _{SAT} CW	r n I	C.C	om				
	$V_{DS} = 50V$							
Output Mismatch Stress ^{*4, 5}	$I_{DQ} = 50 mA$	VSWR	-	-	10:1	ψ		
	$\mathbf{P}_{\mathbf{OUT}} = \mathbf{P}_{\mathbf{SAT}}$ Pulsed							

Electrical Characteristics (Tc=25°C unless otherwise noted)

Note

*1 Measured on wafer prior to packaging.

*2 Scaled from PCM data.

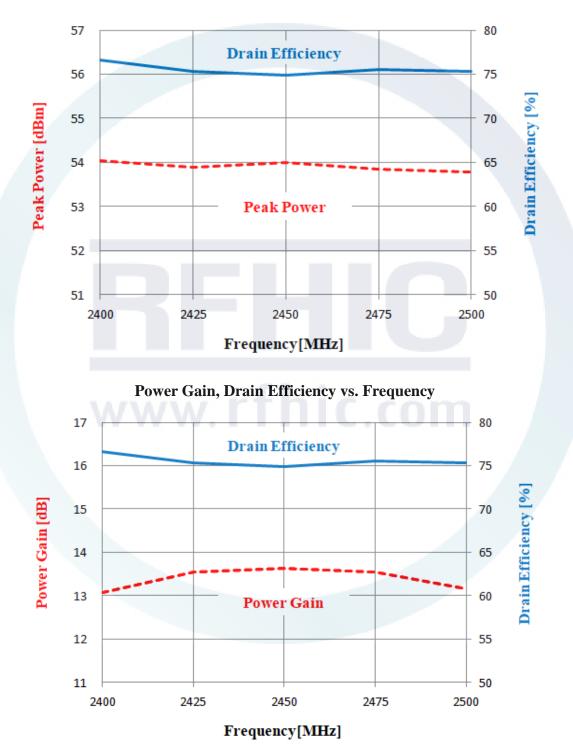
*3 CW(Continuous Wave) signal operation condition.

*4 Pulse width 100usec, Duty Cycle 10%.
*5 Measured in the IE24200P-2450MHz test board amplifier circuit, No damage at all phase angles.

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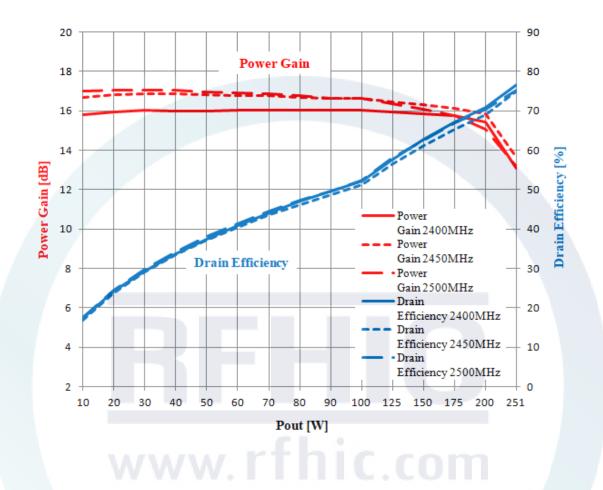
Typical CW Performance Charts

* Bias condition (I_{DQ} =50mA @ V_{DS} =50V, Tc=25°C)



Peak Power, Drain Efficiency vs. Frequency

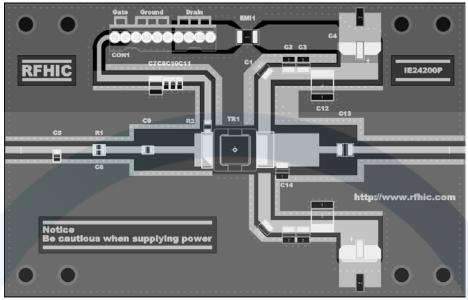
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Power Gain, Drain Efficiency vs. Output Power

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Application Circuit



Part List

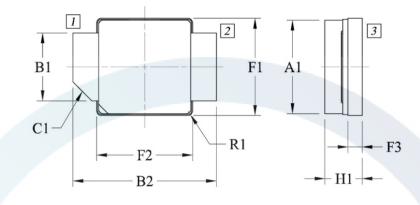
Part	Description	Part Number	Manufacturer
R1	10 Ohm Chip Resistor, 1608	MCR03EZPJ100	ROHM
R2	10 Ohm Chip Resistor, 2012	MCR10EZHJ100	ROHM
C1	2.2uF, 100V MLCC	GRM32ER72A225KA35L	MURATA
C2	10pF High Q Capacitor	501CHB100JSLE	TEMEX
C3	100pF High Q Capacitor	501CHB101JSLE	TEMEX
C4	33uF Aluminum Capacitor	BDS100VC33MJ10TP	SAMYOUNG
C5	1.8pF High Q Capacitor	201CHA1R8CSLE	TEMEX
C6	10pF High Q Capacitor	201CHB100JSLE	TEMEX
C7	10uF, 16V MLCC	C3216X7R1C106K	TDK
C8	1nF Chip Capacitor	GRM188R71H102KA01D	MURATA
С9	1.5pF High Q Capacitor	201CHA1R5BSLE	TEMEX
C10	100pF Chip Capacitor	GRM1885C1H101JA01D	MURATA
C11	10pF Chip Capacitor	GRM1885C1H100JA01D	MURATA
C12	10uF, 100V MLCC	RS80R2A106M	MARUWA
C13	2.7pF High Q Capacitor	501CHB2R7CSLE	TEMEX
C14	0.7pF High Q Capacitor	501CHB0R7BSLE	TEMEX
EMI1	EMI FILTER	CTH32R102S20A-TM	MARUWA
CON1	DC Connector	22-04-1101	MOLEX
РСВ	$\epsilon r = 3.5 \pm 0.05, 0.030$ " (0.762mm)	RF-35TC	TACONIC.
_ TR1	200W GaN Transistor	IE24200P	RFHIC

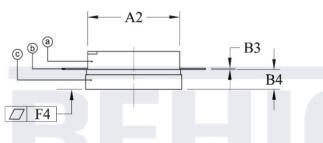
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Package Dimensions (Type : NS-AS01)

* Unit: mm[inch] | Tolerance ± 0.15 [.006]

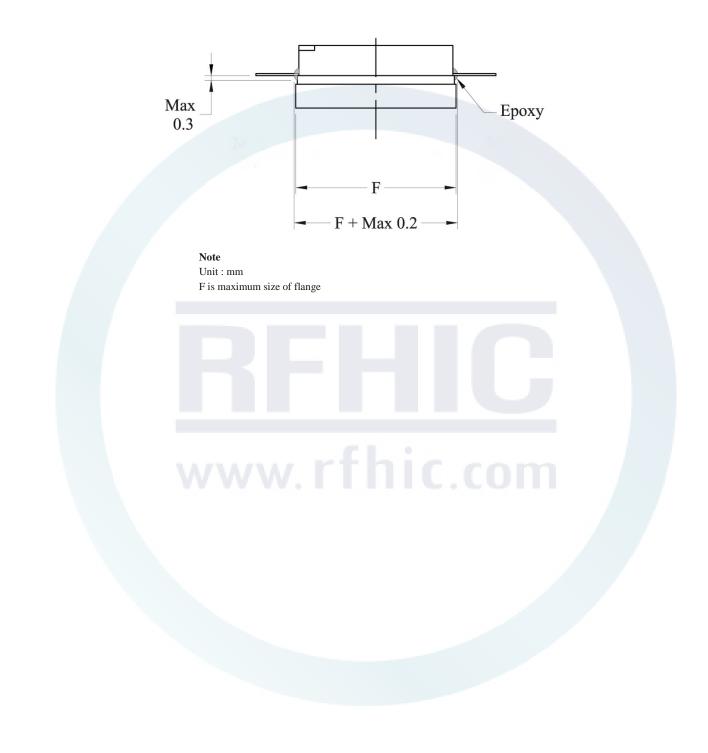




Pin Des	Pin Description		Dim.	INCH			MILLIMETER		
Pin No	Function		Dim.	MIN	ТҮР	MAX	MIN	ТҮР	MAX
I	Gate		A1	.380	.384	.390	9.65	9.75	9.90
2	Drain	W	A2	.380	.384	.390	9.65	9.75	9.90
3	Source		B1	.274	.280	.285	6.97	7.10	7.23
		-	B2	.579	.598	.618	14.70	15.20	15.70
			B3	.004	.005	.007	0.10	0.13	0.18
	(a)- Lid		B4	.080	.085	.090	2.03	2.15	2.28
(b)- Lead Frame			C1 (Chamfer)	.075	.079	.083	1.90	2.00	2.10
	©- Flange		F1	.395	.400	.405	10.03	10.16	10.29
			F2	.395	.400	.405	10.03	10.16	10.29
			F3	.054	.059	.064	1.37	1.50	1.63
			F4	-	.001	-	-	0.03	-
			H1	.148	.159	.167	3.75	4.05	4.25
			L1	-	-	-	-	-	-
			L2	-	-	-	-	-	-
			R1 (Radius)	.016	.020	.024	0.40	0.50	0.60

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Sealing Epoxy Tolerance (Type : NS-AS01)



GaN Power Transistors



Revision History

Part Number	Release Date	Version	Description	Data Sheet Status
IE24200P	April, 2017	0.1	Initial Release of DataSheet	Preliminary
IE24200P	October, 2017	1.0	Revision : Update Test Data	Final



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